

CLAIM AMENDMENTS

IN THE CLAIMS

This listing of the claims will replace all prior versions, and listing, of claims in the application or previous response to office action:

1. **(Currently Amended)** A power semiconductor module comprising a plurality of semiconductor components situated on a substrate, wherein
 - the substrate is divided into a plurality of separate substrate regions, wherein in between two adjacent substrates an area being coplanar with said adjacent substrate regions is defined; and
 - one or a plurality of connecting regions-elements are arranged in said coplanar area between adjacent substrate regions, wherein said connecting region elements are designed to prevent a deformation of one substrate region to continue to an adjacent substrate region.
2. **(Currently Amended)** The power semiconductor module as claimed in claim 1, wherein
 - the connecting regions-elements are formed by recesses in a module housing enclosing said substrate regions.
3. **(Original)** The power semiconductor module as claimed in claim 2, wherein
 - the material recesses are slotted.
4. **(Original)** The power semiconductor module as claimed in claim 1, wherein
 - the substrate is a ceramic.
5. **(Original)** The power semiconductor module as claimed in claim 2, wherein
 - the substrate is a ceramic.
6. **(Canceled)**

7. (Canceled)

8. (Previously Presented) The power semiconductor module as claimed in claim 2, wherein

- the module housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

9. (Previously Presented) The power semiconductor module as claimed in claim 3, wherein

- the module housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

10. (Canceled)

11. (Original) The power semiconductor module as claimed in claim 5, wherein

- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

12. (Previously Presented) The power semiconductor module as claimed in claim 2, wherein

- the housing, at least in the regions of the substrate regions, is such that it acts on the substrate regions with a spring force.

13. (Currently Amended) The power semiconductor module as claimed in claim 1, wherein

- the power semiconductor module has a housing, which, in the region-coplanar area between the substrate regions, has action points for a mechanical pressure application of the connecting regions-elements, and
- the housing applies pressure to the individual substrate regions.

14. (Currently Amended) A power semiconductor module comprising

- a plurality of substrate elements having top and bottom surface and side walls, each substrate element comprising a semiconductor component arranged on the top surface of a substrate element;
- one or a plurality of connecting regions-elements arranged in between adjacent substrate regions to form a continuous bottom surface opposing side walls of two adjacent substrate elements, wherein said connecting region-elements are designed to prevent a deformation of one substrate region to continue to an adjacent substrate region.

15. (Previously Presented) The power semiconductor module as claimed in claim 14, further comprising a module housing enclosing said plurality of substrate elements.

16. (Currently Amended) The power semiconductor module as claimed in claim 15, wherein

- the connecting regions-elements are formed by recesses in the module housing.

17. (Previously Presented) The power semiconductor module as claimed in claim 16, wherein

- the material recesses are slotted.

18. (Previously Presented) The power semiconductor module as claimed in claim 14, wherein

- the substrate is a ceramic.

19. (Previously Presented) The power semiconductor module as claimed in claim 15, wherein

- the module housing, at least in the regions of the substrate elements, is such that it acts on the substrate elements with a spring force.

20. **(Currently Amended)** The power semiconductor module as claimed in claim 14, further comprising

- a heat sink having a flat surface, wherein ~~the continuous-a~~ bottom surface of the plurality of substrate elements and said plurality of connecting regions are arranged on said flat surface.

21. **(Currently Amended)** The power semiconductor module as claimed in claim 15, wherein

- the module housing in ~~the-a~~ region between the substrate elements comprises action points for a mechanical pressure application of the connecting ~~regions-elements~~, and
- the housing applies pressure to the individual substrate elements.

22. **(Currently Amended)** The power semiconductor module as claimed in claim 1, further comprising

- a heat sink having a flat surface, wherein the ~~continuous~~-bottom surface of the plurality of substrate elements and said plurality of connecting ~~regions-elements~~ are arranged on said flat surface.

23. **(Currently Amended)** A power semiconductor module comprising:

- a heat sink having a flat surface,
- a plurality of substrates arranged on the flat surface of the heat sink;
- a plurality of semiconductor components arranged on the substrates,
- one or a plurality of connecting regions arranged directly on the flat surface of the heat sink between adjacent substrate regions, wherein the connecting regions are designed to prevent a deformation of one substrate region to continue to an adjacent substrate region.